

MOSFET - Power, Single N-Channel 35 V, 104 mΩ, 3 A CPH3455

Description

This Power MOSFET is produced using **onsemi**'s trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

Features

- Low On-Resistance
- 4V Drive
- Pb-Free, Halogen Free and RoHS Compliance

Typical Applications

- Load Switch
- Motor Drive

MAXIMUM RATINGS (T_{.I} = 25°C unless otherwise noted) (Note 1)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	35	V
Gate-to-Source Voltage	V_{GSS}	±20	V
Drain Current (DC)	I _D	3	Α
Drain Current (Pulse) PW ≤ 10 μs, duty cycle ≤ 1%	I _{DP}	12	Α
Power Dissipation When mounted on ceramic substrate (900 mm² x 0.8 mm)	P _D	1	W
Junction Temperature	Tj	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

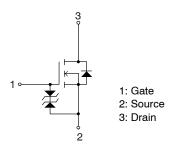
Parameter	Symbol	Value	Unit
Junction-to-Ambient When mounted on ceramic substrate (900 mm ² x 0.8 mm)	$R_{ heta JA}$	125	°C/W

V _{(BR)DSS}	R _{DS(ON)} MAX	I _D MAX
35 V	104 mΩ @ 10 V	3 A
	173 mΩ @ 4.5 V	
	208 mΩ @ 4 V	

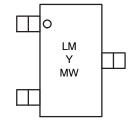


CPH3 CASE 318BA

ELECTRICAL CONNECTION N-Channel



MARKING DIAGRAM



LM = Specific Device Code

Y = Year M = Month W = Week

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

This product is designed to "ESD immunity <200 V*", so please take care when handling.

^{*}Machine Model

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Drain to Source Breakdown Voltage	V _{(BR)DSS}	I _D = 1 mA, V _{GS} = 0 V	35	-	-	V
Zero-Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 35 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μΑ
Gate to Source Leakage Current	I _{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	-		±10	μΑ
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = 10 V, I _D = 1 mA	1.2	-	2.6	V
Forward Transconductance	9FS	V _{DS} = 10 V, I _D = 1.5 A	-	1.7	_	S
Static Drain to Source On–State	R _{DS(on)} 1	I _D = 1.5 A, V _{GS} = 10 V	-	80	104	mΩ
Resistance	R _{DS(on)} 2	I _D = 0.75 A, V _{GS} = 4.5 V	-	123	173	mΩ
	R _{DS(on)} 3	I _D = 0.75 A, V _{GS} = 4 V	_	148	208	mΩ
Input Capacitance	Ci _{SS}	V _{DS} = 20 V, f = 1 MHz	_	186	-	pF
Output Capacitance	Co _{SS}		-	36	-	
Reverse Transfer Capacitance	Cr _{SS}		-	22	-	
Turn-On Delay Time	t _{d(on)}	See specified Test Circuit	-	4.2	-	ns
Rise Time	t _r		-	4.7	-	
Turn-Off Delay Time	t _{d(off)}		-	15	-	
Fall Time	t _f		-	5.7	-	
Total Gate Charge	Qg	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3 \text{ A}$	_	4	-	nC
Gate-to-Source Charge	Q _{gs}		-	0.9	_	
Gate to Drain "Miller" Charge	Q_{gd}		-	0.7	-	
Forward Diode Voltage	V _{SD}	I _S = 3 A, V _{GS} = 0 V	_	0.86	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

SWITCHING TIME TEST CIRCUIT

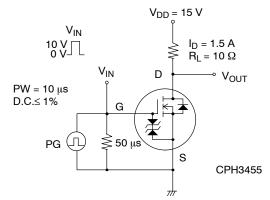
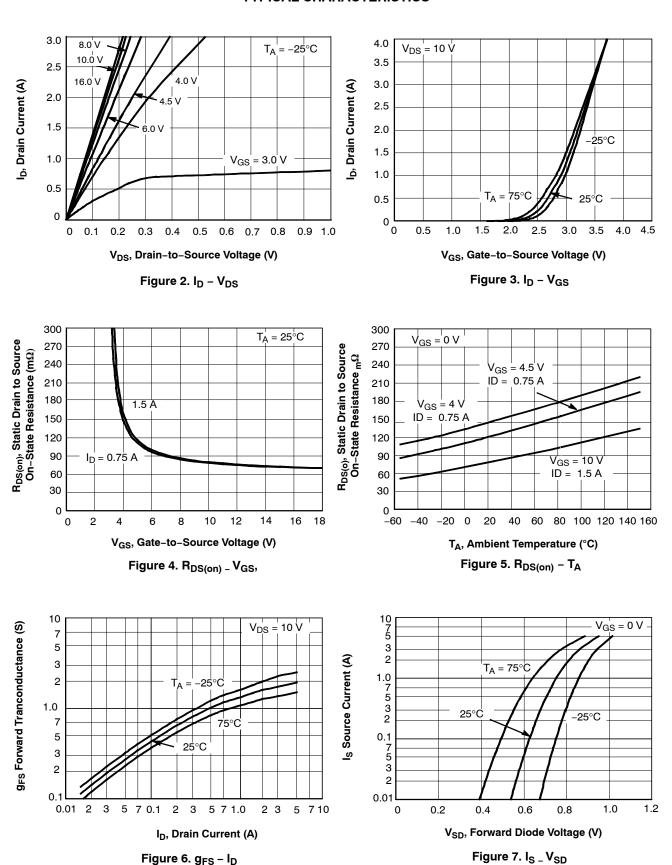


Figure 1. Switching Time Test Circuit

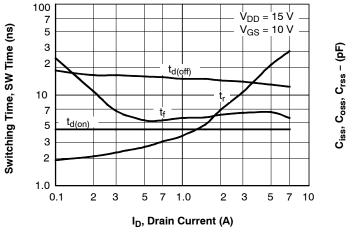
TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (continued)

1000

7

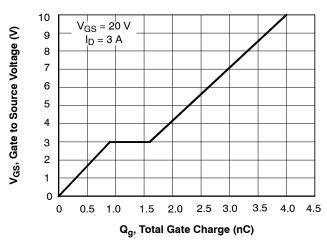


5 C_{iss} 100 5 Coss 3 2 C_{rss} 10 0 5 10 15 20 25 30 35

f = 1 MHz

Figure 8. Time (SW) - I_D

 V_{DS} , Drain-to-Source Voltage (V) Figure 9. V_{DS} - C_{iss} , C_{oss} , C_{rss}



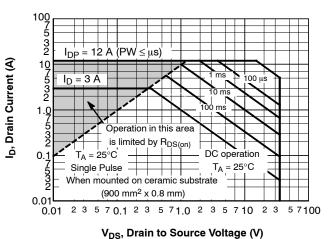


Figure 10. V_{GS} – Q_g

Figure 11. S O A

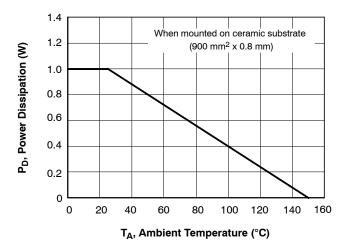


Figure 12. P_D - T_A

TYPICAL CHARACTERISTICS (continued)

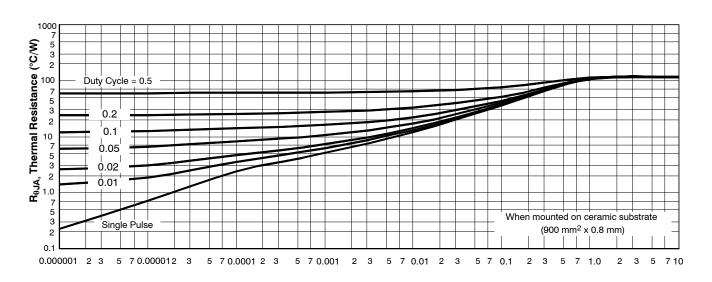


Figure 13. $R_{\theta JA}$ – Pulse Time

Pt Pulse Time (s)

DEVICE ORDERING INFORMATION

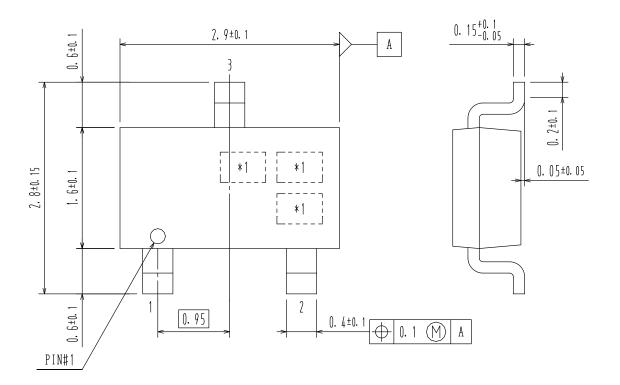
Device	Marking	Package	Shipping [†]
CPH3455-TL-H	LM	CPH3 SC-59, SOT-23, TO-236 (Pb-Free / Halogen Free)	3000 / Tape & Reel

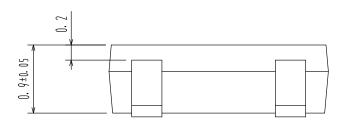
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}Note on usage : Since the CPH3455 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

CPH3 CASE 318BA ISSUE O

DATE 30 NOV 2011





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